

UT3458

Power MOSFET

4.1A, 60V N-CHANNEL
POWER MOSFET

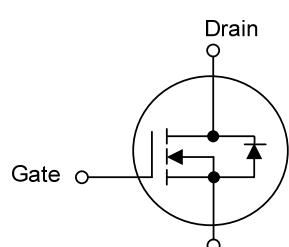
■ DESCRIPTION

The UTC **UT3458** is N-channel enhancement mode power MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$ and low gate charge. This device can be operated with 4.5V low gate voltage.

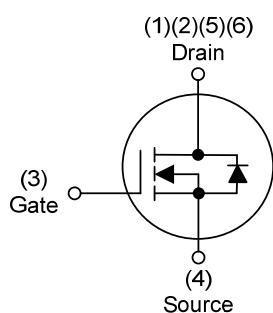
■ FEATURES

* $R_{DS(ON)} \leq 0.1 \Omega$ @ $V_{GS}=10V$, $I_D=3.2A$
 $R_{DS(ON)} \leq 0.128 \Omega$ @ $V_{GS}=4.5V$, $I_D=2.8A$

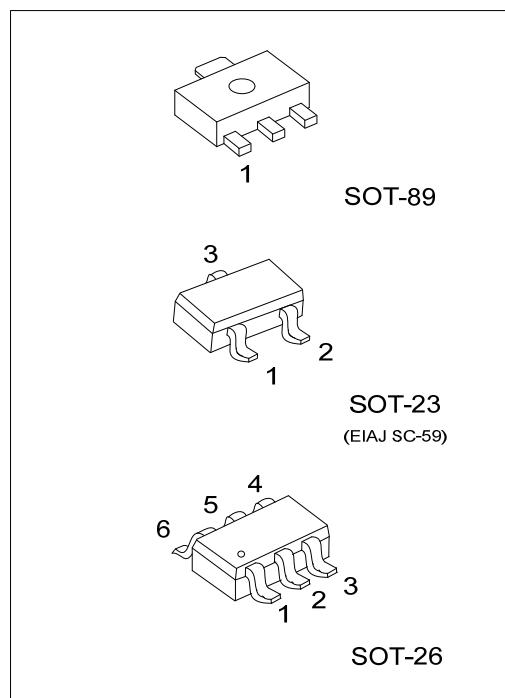
■ SYMBOL



SOT-23/SOT-89



SOT-26



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
UT3458L-AB3-R	UT3458G-AB3-R	SOT-89	G	D	S	-	-	-	Tape Reel
UT3458L-AE3-R	UT3458G-AE3-R	SOT-23	G	S	D	-	-	-	Tape Reel
UT3458L-AG6-R	UT3458G-AG6-R	SOT-26	D	D	G	S	D	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UT3458G-AB3-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AB3: SOT-89, AE3: SOT-23, AG6: SOT-26 (3) G: Halogen Free and Lead Free, L: Lead Free
---------------	--	--

■ MARKING

SOT-89	SOT-23	SOT-26
<p>Date Code UT3458 L: Lead Free G: Halogen Free</p>	<p>34EU L: Lead Free G: Halogen Free</p>	<p>34EU L: Lead Free G: Halogen Free</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current	Continuous (Note 2, 3)	$T_A=25^\circ\text{C}$	I_D	4.1	A
		$T_A=70^\circ\text{C}$		3.2	A
	Pulsed		I_{DM}	15	A
Power Dissipation (Note 2, 3)	SOT-89		P_D	3.3	W
	SOT-23			3.1	W
	SOT-26				
Junction Temperature			T_J	+150	$^\circ\text{C}$
Storage Temperature			T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied..

2. Surface Mounted on FR4 Board.

3. $t \leq 5$ sec.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOT-89	θ_{JA}	105	$^\circ\text{C/W}$
	SOT-23		125	$^\circ\text{C/W}$
	SOT-26			
Junction to Case	SOT-89	θ_{JC}	37	$^\circ\text{C/W}$
	SOT-23		40	$^\circ\text{C/W}$
	SOT-26			

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

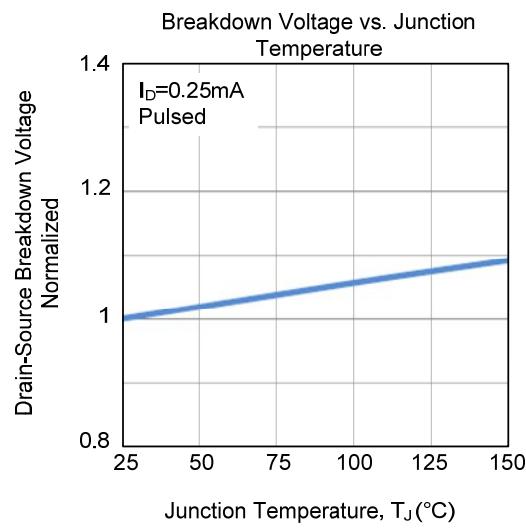
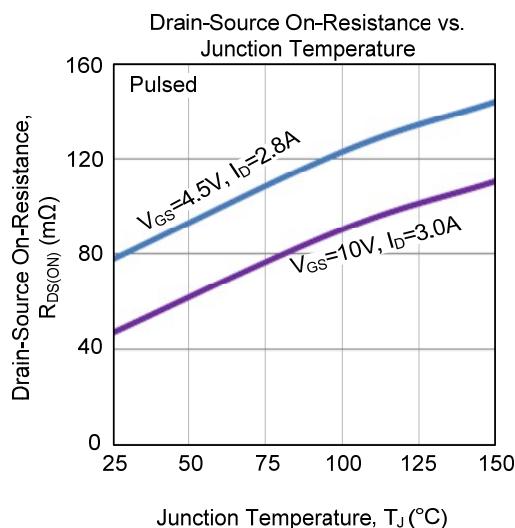
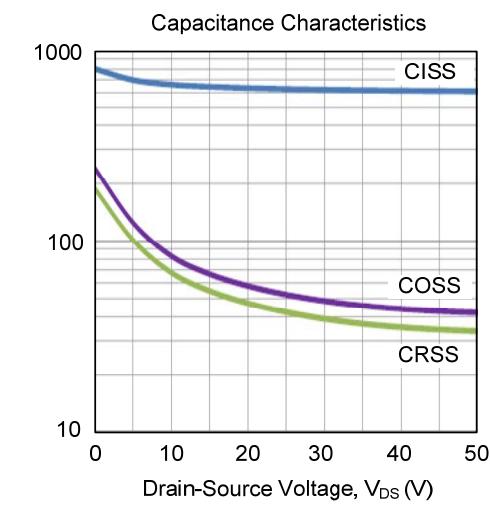
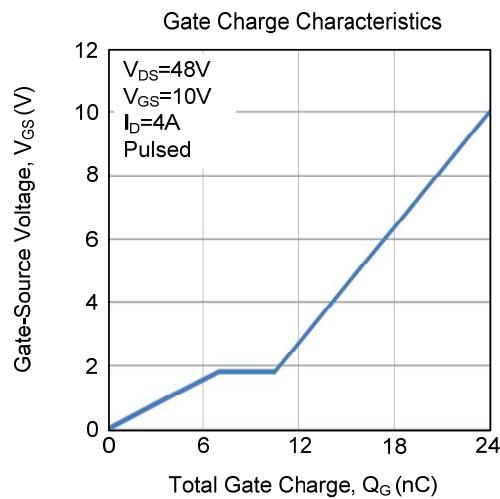
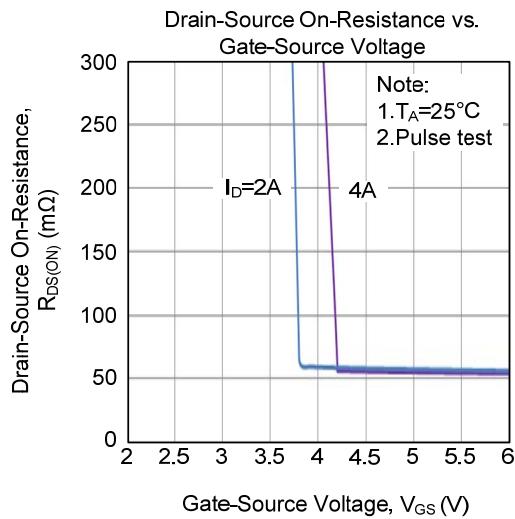
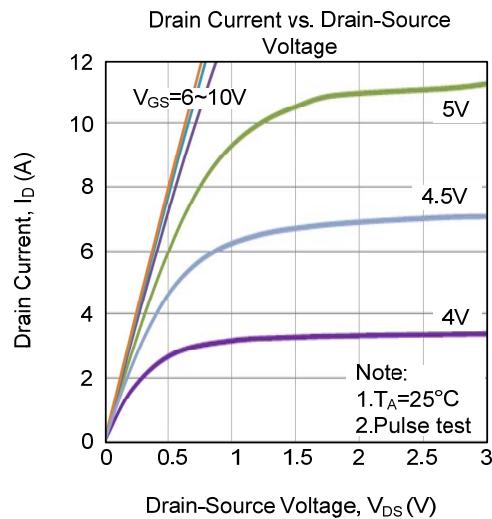
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$			1	μA
Gate- Source Leakage Current	Forward	$V_{GS}=+20\text{V}, V_{DS}=0\text{V}$			+100	nA
	Reverse	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0		3.0	V
Static Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=3.2\text{A}$			0.1	Ω
		$V_{GS}=4.5\text{V}, I_D=2.8\text{A}$			0.128	Ω
SWITCHING PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f = 1\text{MHz}$		630		pF
Output Capacitance	C_{OSS}			52		pF
Reverse Transfer Capacitance	C_{RSS}			42		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS}=48\text{V}, V_{GS}=10\text{V}, I_D=4.0\text{A}$ (Note 1, 2)		24		nC
Gate to Source Charge	Q_{GS}			7		nC
Gate to Drain Charge	Q_{GD}			3.5		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{DS}=30\text{V}, V_{GS}=10\text{V}, I_D=4.0\text{A}, R_G=3.3\Omega$ (Note 1, 2)		7		nC
Rise Time	t_R			16		nC
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			18		nC
Fall Time	t_F			20		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				2.9	A
Maximum Body-Diode Pulsed Current	I_{SM}				10	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=2.5\text{A}, V_{GS}=0\text{V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=4.0\text{A}, V_{GS}=0\text{V}, dI_F/dt=100\text{A}/\mu\text{s}$		50		ns
Body Diode Reverse Recovery Charge	Q_{rr}			42		nC

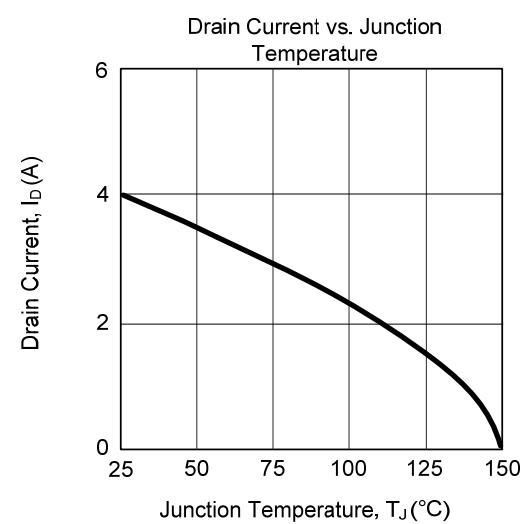
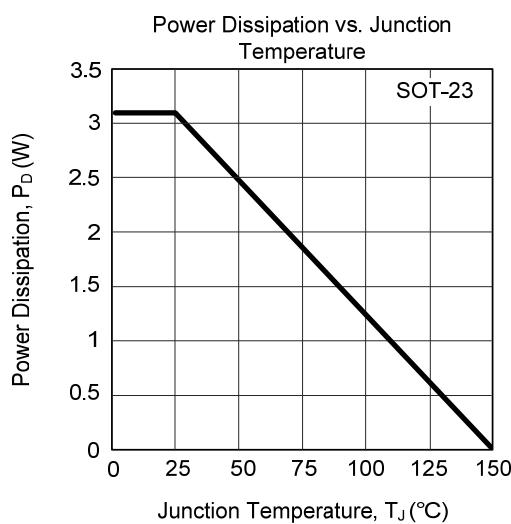
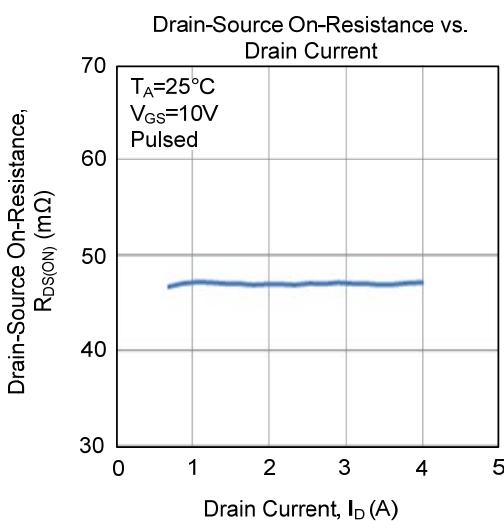
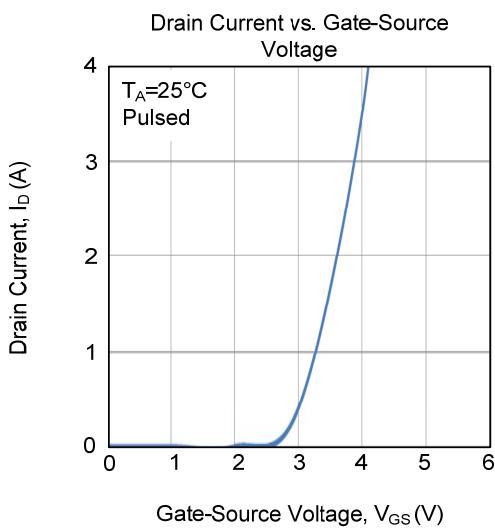
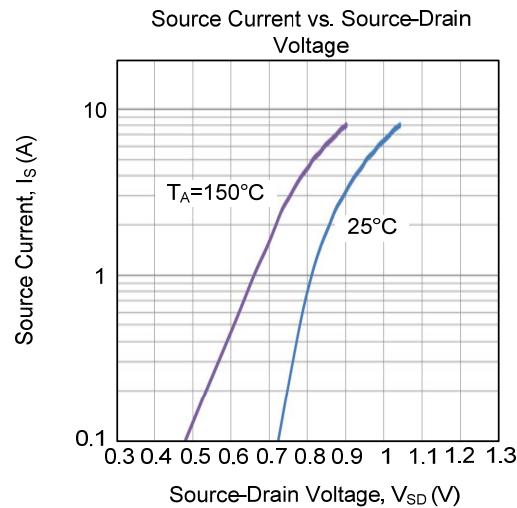
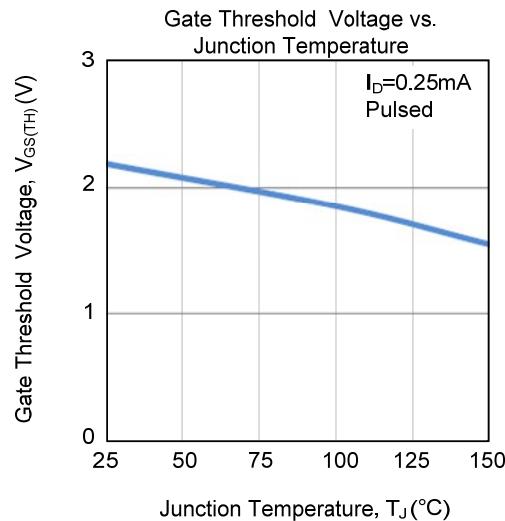
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Guaranteed by design, not subject to production testing.

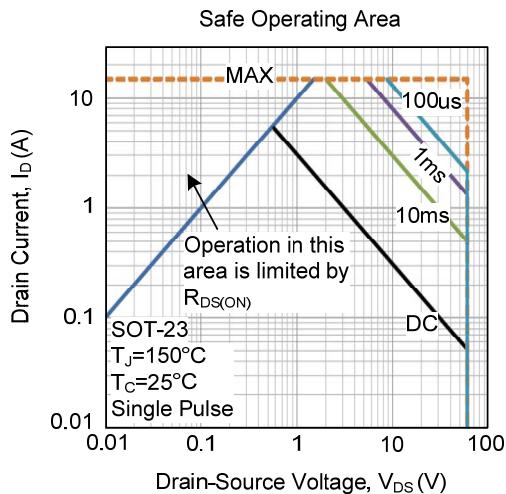
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.